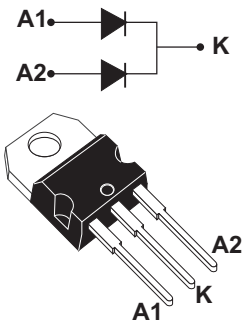
STPSC8H065C

650 V power Schottky silicon carbide diode

Datasheet - production data



TO-220AB
STPSC8H065CT

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- High forward surge capability

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimized capacitive charge at turn-off behavior is independent of temperature.

Especially suited for use in interleaved or bridge-less topologies, this dual-diode rectifier will boost the performance in hard switching conditions. Its high forward surge capability ensures a good robustness during transient phases.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 4 A
V_{RRM}	650 V
T_j (max)	175 °C

1 Characteristics

Table 2. Absolute ratings (limiting values per diode at 25 °C unless otherwise specified)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			650	V
$I_{F(RMS)}$	Forward rms current			22	A
$I_{F(AV)}$	Average forward current	T_c = 145 °C(1), DC	Per diode	4	A
		T_c = 145 °C(2), DC	Per device	8	A
I_{FSM}	Surge non repetitive forward current	t_p = 10 ms sinusoidal, T_c = 25 °C t_p = 10 ms sinusoidal, T_c = 125 °C t_p = 10 µs square, T_c = 25 °C		38 35 200	A
I_{FRM}	Repetitive peak forward current	T_c = 145 °C(1),T_j = 175 °C, δ = 0.1		17	A
T_{stg}	Storage temperature range			-65 to +175	°C
T_j	Operating junction temperature(3)			-40 to +175	°C

1. Value based on $R_{th(j-c)}$ max (per diode)
2. Value based on $R_{th(j-c)}$ max (per device)
3. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance parameters

Symbol	Parameter		Typ.	Max.	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.8	2.7	°C/W
		Per device	0.95	1.40	
$R_{th(c)}$	Coupling		-	0.1	

When the diodes 1 and 2 are used simultaneously:
ΔT_j(diode 1) = P(diode1) x $R_{th(j-c)}$(Per diode) + P(diode2) x $R_{th(c)}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R (1)	Reverse leakage current	T_j = 25 °C	$V_R = V_{RRM}$	-	3	40	µA
		T_j = 150 °C		-	35	170	
V_F (2)	Forward voltage drop	T_j = 25 °C	I_F = 4 A	-	1.56	1.75	V
		T_j = 150 °C		-	1.98	2.5	

1. t_p = 10 ms, δ < 2%
2. t_p = 500 µs, δ < 2%

To evaluate the conduction losses use the following equation:

$P = 1.35 \times I_{F(AV)} + 0.288 \times I_F{}^2{}_{(RMS)}$

Table 5. Dynamic electrical characteristics (per diode)

Symbol	Parameter	Test conditions	Typ.	Unit
Q_{cj}(1)	Total capacitive charge	V_R = 400 V	12.5	nC
C_j	Total capacitance	V_R = 0 V, T_c = 25 °C, F = 1 MHz	200	pF
		V_R = 400 V, T_c = 25 °C, F = 1 MHz	21	

1. Most accurate value for the capacitive charge: $Q_{cj} = \int_0^{V_{OUT}} c_j(v_R).dv_R$

Figure 1. Forward voltage drop versus forward current (typical values, low level, per diode)

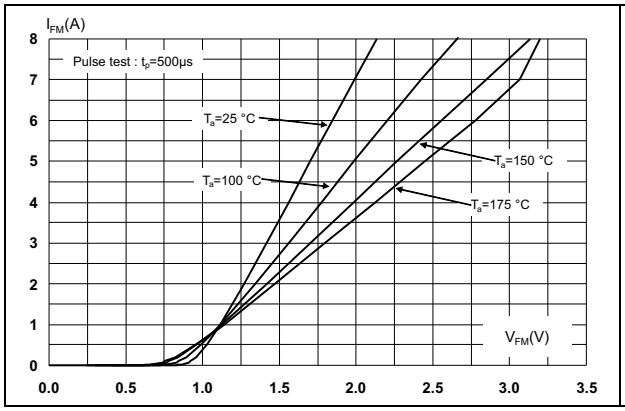


Figure 2. Forward voltage drop versus forward current (typical values, high level, per diode)

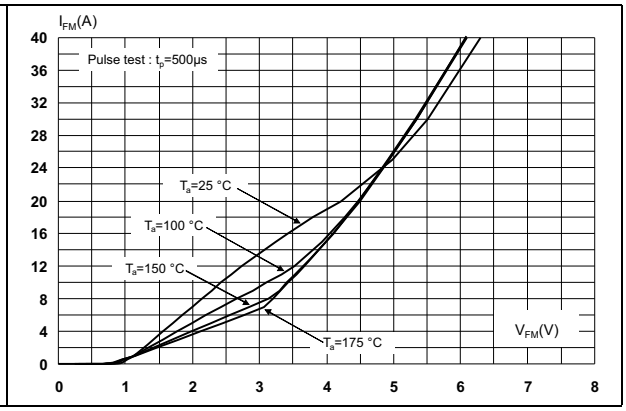


Figure 3. Reverse leakage current versus reverse voltage applied (typical values, per diode)

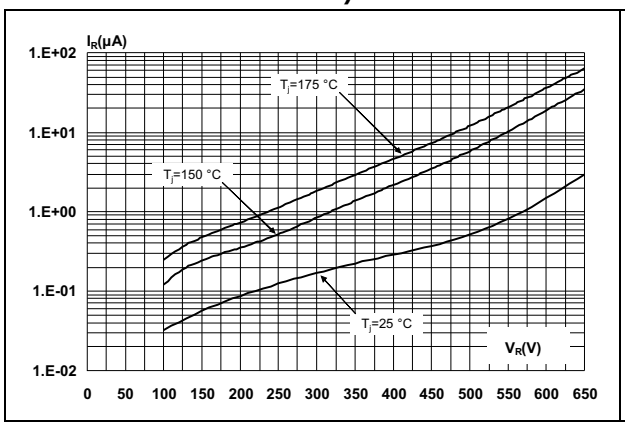


Figure 4. Peak forward current versus case temperature (per diode)

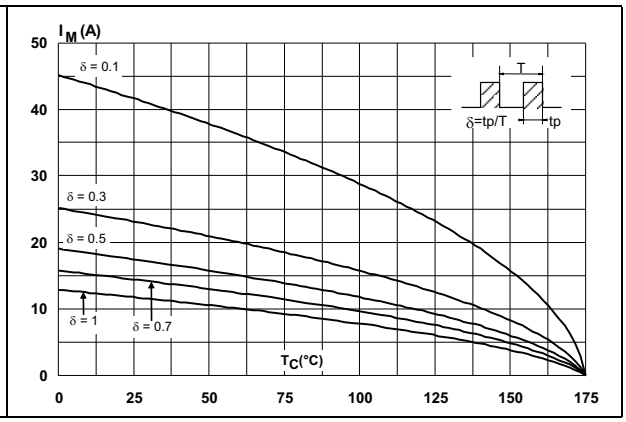


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

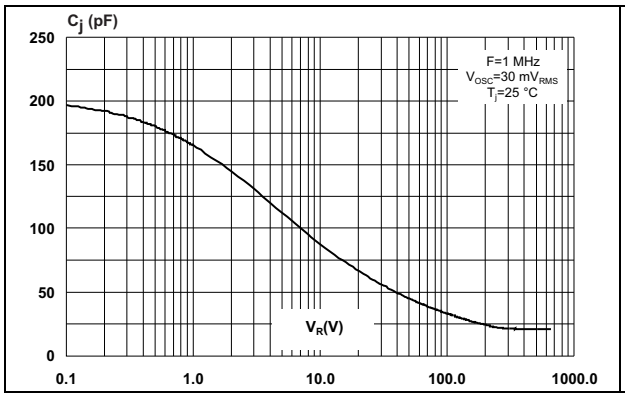


Figure 6. Relative variation of thermal impedance junction to case versus pulse duration

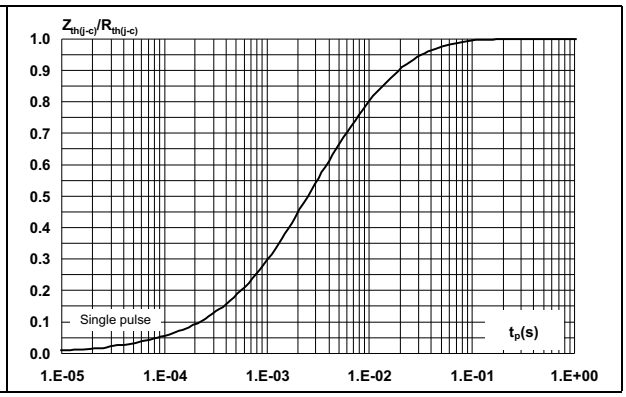


Figure 7. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform, per diode)

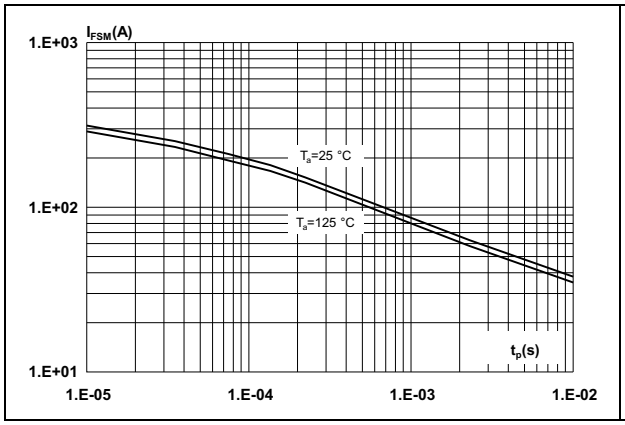
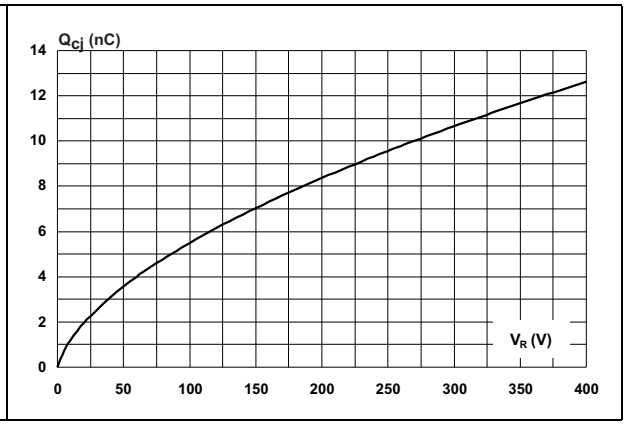


Figure 8. Total capacitive charges versus reverse voltage applied (typical values, per diode)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

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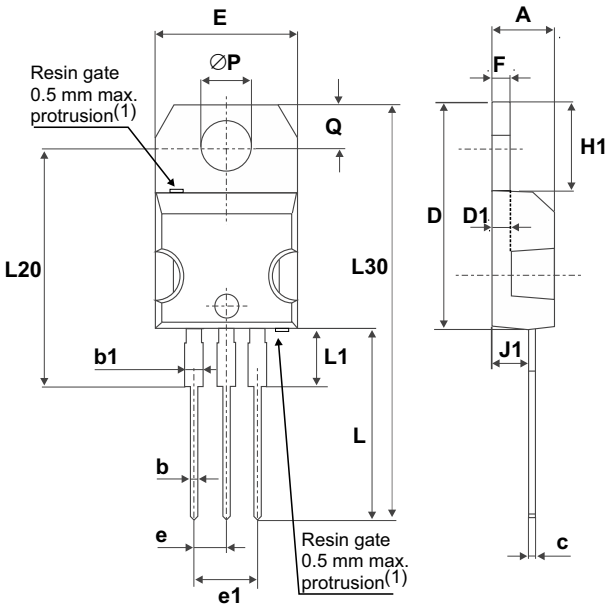
Figure 9. TO-220AB dimension definitions



(1) Resin gate position accepted in each of the two position shown as well as the symmetrical opposites

Table 6. TO-220AB dimensions values

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.17	0.18
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.045	0.067
c	0.48	0.70	0.019	0.027
D	15.25	15.75	0.60	0.62
D1	1.27 typ.		0.05 typ.	
E	10	10.40	0.39	0.41
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.19	0.20
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.24	0.26
J1	2.40	2.72	0.094	0.107
L	13	14	0.51	0.55
L1	3.50	3.93	0.137	0.154
L20	16.40 typ.		0.64 typ.	
L30	28.90 typ.		1.13 typ.	
∅P	3.75	3.85	0.147	0.151
Q	2.65	2.95	0.104	0.116

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC8H065CT	STPSC8H065CT	TO-220AB	1.86 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Jun-2013	1	First issue.
07-Nov-2013	2	Updated *Figure 1* and *Figure 2*.

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